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- Member of the Texas Instruments Widebus™ Family
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- B-Port Outputs Have Equivalent 26-Ω
 Series Resistors, So No External Resistors
 Are Required
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

NOTE: For tape and reel order entry:
The DGGR package is abbreviated to GR.

description

This 12-bit to 24-bit registered bus exchanger is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74ALVCH162268 is used for applications in which data must be transferred from a narrow high-speed bus to a wide, lower-frequency bus.

The device provides synchronous data exchange between the two ports. Data is stored in the internal registers on the low-to-high transition of the clock (CLK) input when the appropriate clock-enable (CLKEN) inputs are low. The select (SEL) line is synchronous with CLK and selects 1B or 2B input data for the A outputs.

DGG OR DL PACKAGE (TOP VIEW)

OEA [1	\cup	56	OEB
CLKEN1B [2			CLKENA2
2B3 [3		54] 2B4
GND [4		53	GND
2B2 [5		52] 2B5
2B1 [6		51] 2B6
V _{CC} [7		50]v _{cc}
A1 [49] 2B7
A2 [9		48] 2B8
A3 [10		47] 2B9
GND [11		46] GND
A4 [12		45	2B10
A5 [44] 2B11
A6 [14		43	2B12
A7 [15		42]1B12
A8 [16] 1B11
A9 [17		40] 1B10
GND [18		39] GND
A10 [19		38] 1B9
A11 [20		37] 1B8
A12 [21		36] 1B7
V _{CC} [22		35]v _{cc}
1B1 [] 1B6
1B2 [] 1B5
GND [] GND
1B3 [] <u>1B4</u>
CLKEN2B [27		30	CLKENA1
SEL [28		29]CLK
•				•

For data transfer in the A-to-B direction, a two-stage pipeline is provided in the A-to-1B path, with a single storage register in the A-to-2B path. Proper control of these inputs allows two sequential 12-bit words to be presented synchronously as a 24-bit word on the B port. Data flow is controlled by the active-low output enables (OEA, OEB). These control terminals are registered, so bus direction changes are synchronous with CLK.

The B outputs, which are designed to sink up to 12 mA, include equivalent $26-\Omega$ resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, a clock pulse should be applied as soon as possible and \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver. Due to \overline{OE} being routed through a register, the active state of the outputs cannot be determined prior to the arrival of the first clock pulse.



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description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162268 is characterized for operation from -40°C to 85°C.

Function Tables

OUTPUT ENABLE

	INPUTS		OUT	PUTS
CLK	OEA	OEB	Α	1B, 2B
1	Н	Н	Z	Z
1	Н	L	Z	Active
1	L	Н	Active	Z
1	L	L	Active	Active

A-TO-B STORAGE (OEB = L)

	INPUTS					
CLKENA1	CLKENA2	CLK	Α	1B	2B	
Н	Н	Χ	Χ	1B ₀ ‡	2B ₀ ‡	
L	L	\uparrow	L	L†	X	
L	L	\uparrow	Н	H [†]	Χ	
X	L	\uparrow	L	Х	L	
X	L	\uparrow	Н	Х	Н	

[†]Two CLK edges are needed to propagate data.

B-TO-A STORAGE (OEA = L)

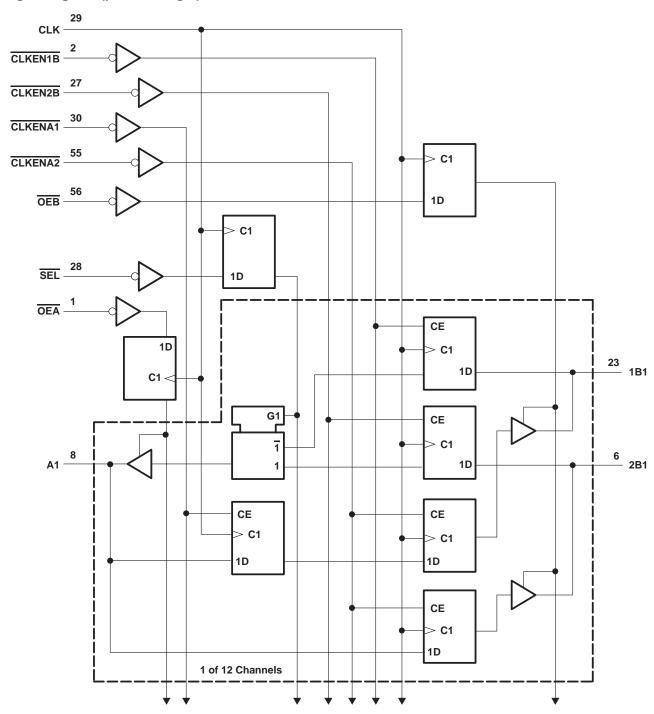
	INPUTS								
CLKEN1B	CLKEN2B	CLK	SEL	1B	2B	Α			
Н	Х	Χ	Н	Х	Х	A ₀ ‡			
Х	Н	Χ	L	Χ	X	A ₀ ‡			
L	L	\uparrow	Н	L	X	L			
L	L	\uparrow	Н	Н	X	Н			
Х	L	\uparrow	L	Χ	L	L			
Х	L	↑	L	Χ	Н	Н			

[‡]Output level before the indicated steady-state input conditions were established



[‡]Output level before the indicated steady-state input conditions were established

logic diagram (positive logic)



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	0.5 V to 4.6 V
Input voltage range, V _I : Except I/O ports (see Note 1)	–0.5 V to 4.6 V
I/O ports (see Notes 1 and 2)	0.5 V to V_{CC} + 0.5 V
Output voltage range, VO (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, $I_{ K }(V_{ } < 0)$	
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	81°C/W
DL package	74°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.



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recommended operating conditions (see Note 4)

			MIN	MAX	UNIT		
VCC	Supply voltage		1.65	3.6	V		
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	$0.65 \times V_{CC}$				
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V		
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2				
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		0.35 × V _{CC}			
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V		
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8			
٧ _I	Input voltage		0	VCC	V		
٧o	Output voltage		0	Vcc	V		
		V _{CC} = 1.65 V		-4			
	High-level output current (A port)	V _{CC} = 2.3 V		-12			
		V _{CC} = 2.7 V		-12	A		
		V _{CC} = 3 V		-24			
IOH	High-level output current (B port)	V _{CC} = 1.65 V		-2	mA		
		V _{CC} = 2.3 V		-6	ĺ		
		V _{CC} = 2.7 V		-8			
		V _{CC} = 3 V		-12			
		V _{CC} = 1.65 V		4			
	Low level output ourrent (A port)	V _{CC} = 2.3 V		12			
	Low-level output current (A port)	V _{CC} = 2.7 V	12 24		1		
la.		V _{CC} = 3 V			m Λ		
IOL		V _{CC} = 1.65 V		2	mA		
	Law law law and a ware and (D a seal)	V _{CC} = 2.3 V	6				
	Low-level output current (B port)	V _{CC} = 2.7 V		8			
	V _{CC} = 3 V			12			
Δt/Δν	Input transition rise or fall rate			10	ns/V		
T _A	Operating free-air temperature	-	-40	85	°C		

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAI	RAMETER	TEST CONDITIONS	Vcc	MIN	TYP [†] MAX	UNIT
		I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2	2	
		$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		1
		$I_{OH} = -6 \text{ mA}$	2.3 V	2		1
	A port		2.3 V	1.7		1
		I _{OH} = -12 mA	2.7 V	2.2		1
			3 V	2.4		1
.,		I _{OH} = -24 mA	3 V	2		1 ,,
VOH		I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2	2	-
		$I_{OH} = -2 \text{ mA}$	1.65 V	1.2		1
		$I_{OH} = -4 \text{ mA}$	2.3 V	1.9		1
	B port		2.3 V	1.7		1
		IOH = -6 mA	3 V	2.4		1
		$I_{OH} = -8 \text{ mA}$	2.7 V	2		1
		I _{OH} = -12 mA	3 V	2		1
		I _{OL} = 100 μA	1.65 V to 3.6 V		0.2	1
		I _{OL} = 4 mA	1.65 V		0.45	1
	. .	I _{OL} = 6 mA	2.3 V		0.4	1
	A port		2.3 V		0.7	1
		I _{OL} = 12 mA	2.7 V		0.4	1
		I _{OL} = 24 mA	3 V		0.55	1
VOL		I _{OL} = 100 μA	1.65 V to 3.6 V		0.2	V
		I _{OL} = 2 mA	1.65 V		0.45	1
		I _{OL} = 4 mA	2.3 V		0.4	1
	B port	1 0 4	2.3 V		0.55	1
		IOL = 6 mA	3 V		0.55	1
		I _{OL} = 8 mA	2.7 V		0.6	1
		I _{OL} = 12 mA	3 V		0.8	1
ΙĮ		V _I = V _{CC} or GND	3.6 V		±5	μА
		V _I = 0.58 V	4.05.1/	25		
		V _I = 1.07 V	1.65 V	-25		1
		V _I = 0.7 V	0.014	45		1
I _{I(hold)}		V _I = 1.7 V	2.3 V	-45		μΑ
, ,		V _I = 0.8 V	2)/	75		1
		V _I = 2 V	3 V	-75		1
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$	3.6 V		±500	1
I _{OZ} §		$V_O = V_{CC}$ or GND	3.6 V		±10	μΑ
Icc		$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V		40	μА
Δlcc		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 3.6 V		750	μА
Ci	Control inputs	V _I = V _{CC} or GND	3.3 V		3.5	pF
C _{io}	A or B ports	V _O = V _{CC} or GND	3.3 V		9	pF

 $[\]mbox{\$ For I/O ports, the parameter IOZ}$ includes the input leakage current.



[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

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timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

			V _{CC} =	1.8 V	V _{CC} =		V _{CC} =	2.7 V	V _{CC} =		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock freque	ency		†		120		125		150	MHz
t _W	Pulse durati	on, CLK high or low	†		3.3		3.3		3.3		ns
		A data before CLK↑	†		4.5		4		3.4		
		B data before CLK↑	†		0.8		1.2		1		
١.	Setup time	SEL before CLK↑	†		1.4		1.6		1.3		ns
t _{su}		CLKENA1 or CLKENA2 before CLK↑	†		3.6		3.4		2.8		115
		CLKENB1 or CLKENB2 before CLK↑	†		3.2		3		2.5		
		OE before CLK↑	†		4.2		3.9		3.2		
		A data after CLK↑	†		0		0		0.2		
		B data after CLK↑	†		1.3		1.2		1.3		
.	Hold time	SEL after CLK↑	†		1		1		1		
th	noia time	CLKENA1 or CLKENA2 after CLK↑	†		0.1		0.1		0.4		ns
		CLKENB1 or CLKENB2 after CLK↑	†		0.1		0		0.5		
		OE after CLK↑ after CLK↑	†		0		0		0.2		

[†] This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM TO				V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INPUT)	(OUTPUT)	MIN	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			†		120		125		150		MHz
		В		†	1.6	6.1		5.9	1.8	5.4	
	CLK	A (1B)		†	1.6	5.8		5.4	1.7	4.8	
^t pd		A (2B)		†	1.6	5.8		5.3	1.8	4.8	ns
		A (SEL)		†	2.5	7.3		6.5	2.4	5.8	
t _{en}	CLK	В		†	2.7	7.2		6.8	2.6	6.1	ns
^t dis	CLK	В		†	2.8	7.2		6.1	2.5	5.9	ns
t _{en}	CLK	А		†	2	6.2		5.6	1.8	5.1	ns
^t dis	CLK	А		†	2	6.5		5.4	2.1	5	ns

[†] This information was not available at the time of publication.

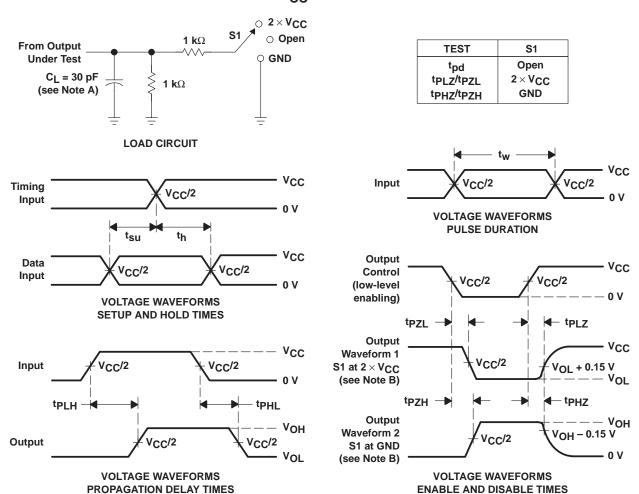
operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V _{CC} = 1.8 V V _{CC} = 2.5 V V _{CC} =		V _{CC} = 3.3 V	UNIT	
	FARAMETER		TEST CONDITIONS	TYP	TYP	TYP	UNII	
	Power dissipation	Outputs enabled	C ₁ = 50 pF. f = 10 MHz	†	87	120	pF	
Cpd	capacitance	Outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	†	80.5	118	pΓ	

[†] This information was not available at the time of publication.



PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V



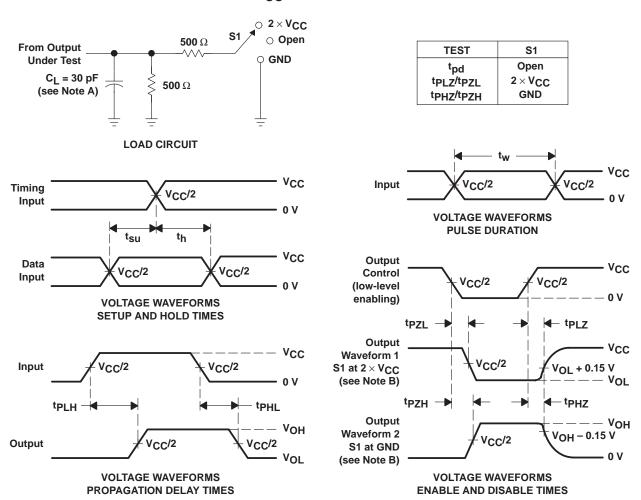
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2 ns$, $t_f \leq 2 ns$.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as t_{dis}.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 V \pm 0.2 V$

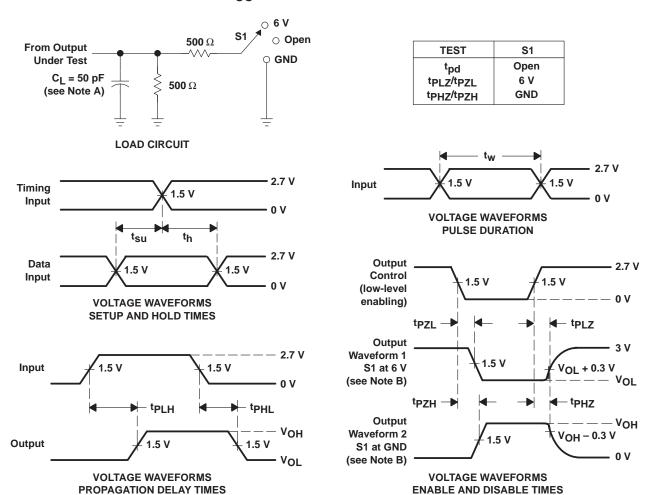


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{O} = 50 $\Omega,\,t_{f}$ \leq 2 ns, t_{f} \leq 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpl H and tpHI are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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